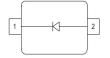


## Silicon Variable Capacitance Diodes

- For tuning of extended frequency band in VHF TV / VTR tuners
- High capacitance ratio
- Low series inductance
- Low series resistance
- Excellent uniformity and matching due to "in-line" matching assembly procedure
- Pb-free (RoHS compliant) package



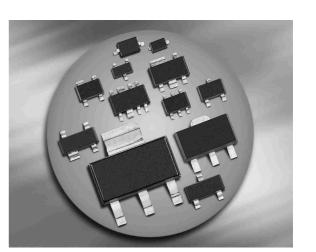
#### BB639 BB659



Туре	Package	Configuration	<b>L<sub>S</sub></b> (nH)	Marking
BB639	SOD323	single	1.8	yellow S
BB659	SCD80	single	0.6	DE

## **Maximum Ratings** at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Diode reverse voltage	V <sub>R</sub>	30	V	
Peak reverse voltage	V <sub>RM</sub>	35		
( $R \ge 5 \mathrm{k}\Omega$ )				
Forward current	I <sub>F</sub>	20	mA	
Operating temperature range	T <sub>op</sub>	-55 150	°C	
Storage temperature	T <sub>stg</sub>	-55 150		





Parameter	Symbol		Values		
		min.	typ.	max.	]
DC Characteristics					
Reverse current	I <sub>R</sub>				nA
<i>V</i> <sub>R</sub> = 30 V		-	-	10	
V <sub>R</sub> = 30 V, <i>T</i> <sub>A</sub> = 85 °C		-	-	200	
AC Characteristics					
Diode capacitance	CT				pF
$V_{\rm R}$ = 1 V, <i>f</i> = 1 MHz		36	38.3	40	
$V_{R} = 2 V, f = 1 MHz$		27.7	29.75	31.8	
$V_{\rm R}$ = 25 V, <i>f</i> = 1 MHz		2.5	2.85	3.2	
$V_{\rm R}$ = 28 V, <i>f</i> = 1 MHz		2.4	2.6	2.9	
Capacitance ratio	C <sub>T1</sub> /C <sub>T28</sub>	13.5	14.7	-	
V <sub>R</sub> = 1 V, V <sub>R</sub> = 28 V, <i>f</i> = 1 MHz					
Capacitance ratio	C <sub>T2</sub> /C <sub>T25</sub>	9.8	10.4	-	
$V_{\rm R}$ = 2 V, $V_{\rm R}$ = 25 V, $f$ = 1 MHz					
Capacitance matching <sup>1)</sup>	$\Delta C_{\rm T}/C_{\rm T}$				%
$V_{\rm R}$ = 1 V, $V_{\rm R}$ = 28 V, $f$ = 1 MHz, 7 diode sequence	-				
BB639		-	-	2.5	
$V_{\rm R}$ = 1 V, $V_{\rm R}$ = 28 V, $f$ = 1 MHz, <b>4</b> diode sequence					
BB659		-	0.3	1	
$V_{\rm R}$ = 1 V, $V_{\rm R}$ = 28 V, $f$ = 1 MHz, 7 diode sequence					
BB659		-	0.4	2	
Series resistance	r <sub>S</sub>	-	0.65	0.7	Ω
V <sub>R</sub> = 5 V, <i>f</i> = 470 MHz					

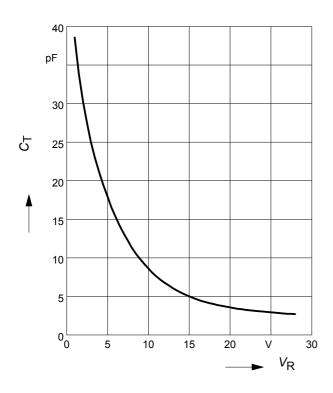
## **Electrical Characteristics** at $T_A = 25^{\circ}$ C, unless otherwise specified

<sup>1</sup>For details please refer to Application Note 047.



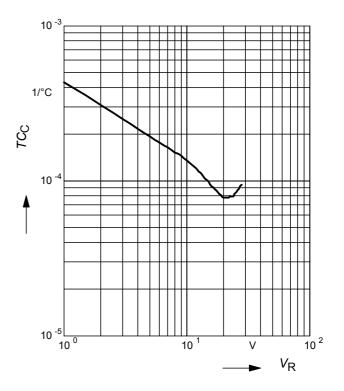
## **Diode capacitance** $C_{T} = f(V_{R})$

f = 1 MHz



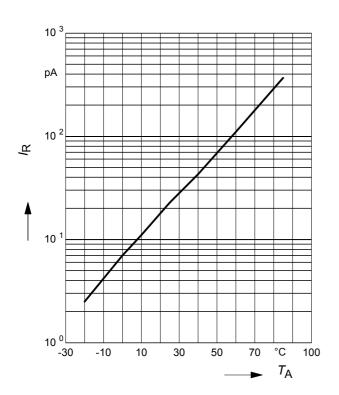
Temperature coefficient of the diode

capacitance  $T_{Cc} = f(V_R)$ 

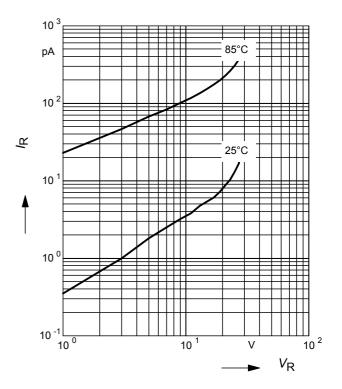




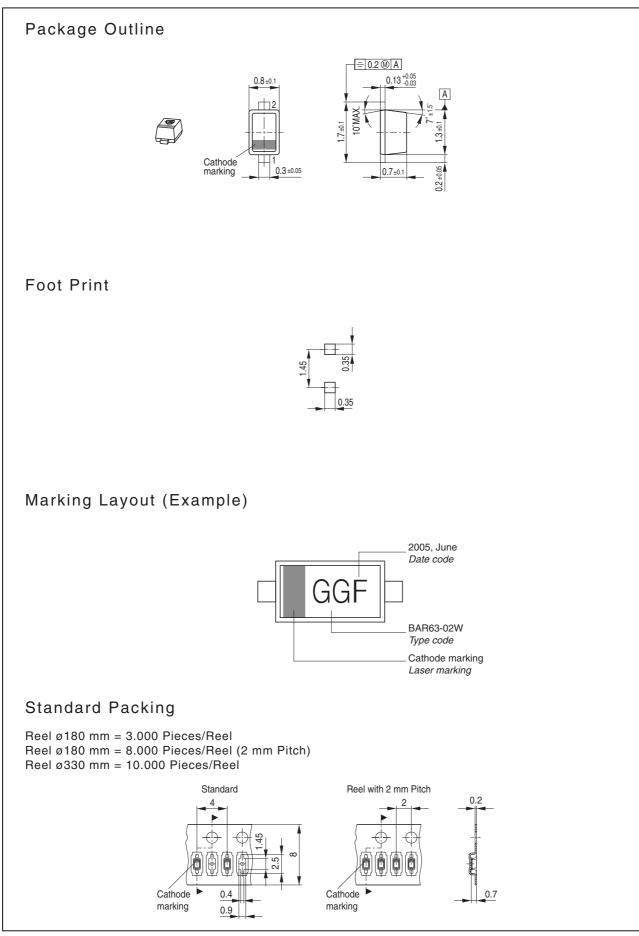
*V*<sub>R</sub> = 28V



**Reverse current**  $I_{R} = f(V_{R})$  $T_{A}$  = Parameter







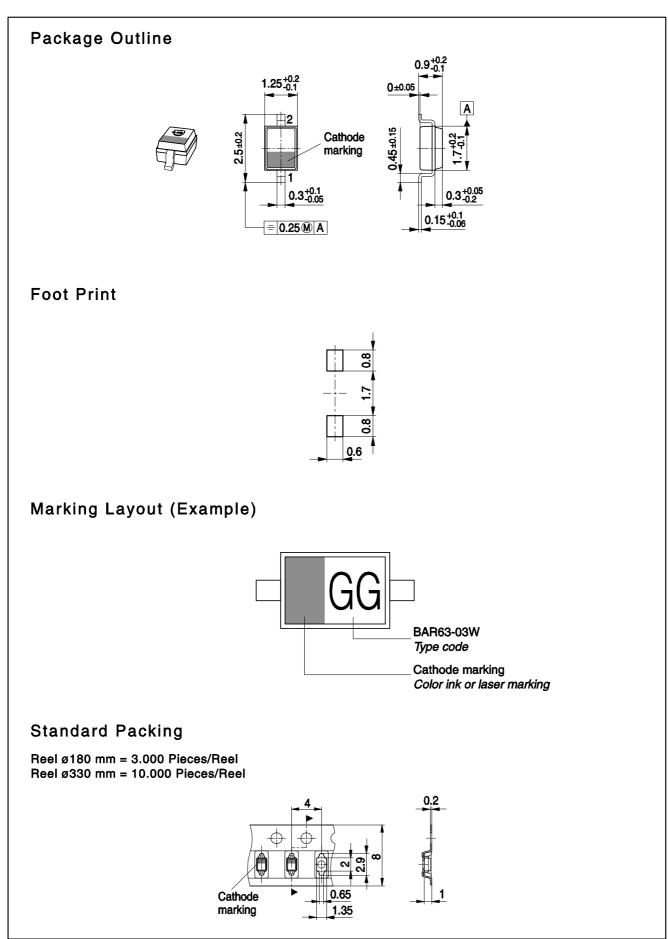


# Date Code marking for discrete packages with one digit (SCD80, SC79, SC75<sup>1</sup>) CES-Code

Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	а	р	А	Р	а	р	А	Р	а	р	А	Р
02	b	q	В	Q	b	q	В	Q	b	q	В	Q
03	С	r	С	R	С	r	С	R	С	r	С	R
04	d	S	D	S	d	S	D	S	d	S	D	S
05	е	t	E	Т	е	t	E	Т	е	t	Е	Т
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	V	G	V	g	V	G	V	g	V	G	V
08	h	х	Н	Х	h	х	Н	Х	h	х	Н	Х
09	j	у	J	Y	j	у	J	Y	j	у	J	Y
10	k	Z	K	Z	k	Z	K	Z	k	Z	K	Z
11	I	2	L	4	I	2	L	4	I	2	L	4
12	n	3	Ν	5	n	3	Ν	5	n	3	Ν	5

1) New Marking Layout for SC75, implemented at October 2005.







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